QM18N20D

N-Channel 200V Fast Switching MOSFET

General Description

The QM18N20D is a high performance N-channel MOSFET which utilizes high voltage technology to provide low Rdson and gate charge characteristics. It is ideally suited to support most of SPS, Charger, Adapter and LED lighting applications.

The QM18N20D meets RoHS and Green Product requirements while supporting full function reliability.

Features

- ✓ Super Low Gate Charge
- ✓ Excellent CdV/dt effect decline
- ✓ Green Device Available

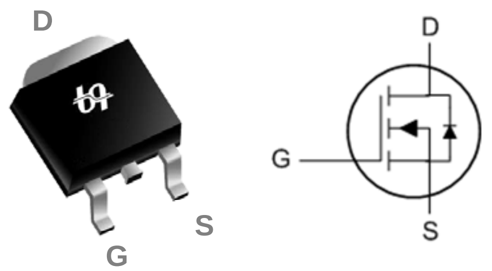
Product Summary

V_{DS}	$R_{DS(ON)}$ max (V_{GS}=10V)	I_D (T_C=25 °C)
200V	190 mΩ	18A

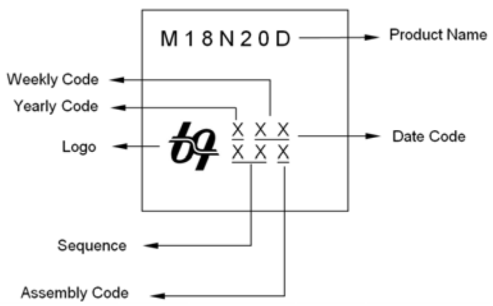
Applications

- ✓ High efficient switched mode power supplies
- ✓ Electronic lamp ballast
- ✓ LCD TV/ Monitor
- ✓ Adapter

Pin Configuration



Ordering Information

Order Number	Package Type	Top Marking
QM18N20D	TO252	

QM18N20D

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage	±30	V
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ 10V[1]	18	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ 10V[1]	11.4	A
I_{DM}	Pulsed Drain Current[2]	36	A
EAS	Single Pulse Avalanche Energy[3]	187	mJ
I_{AS}	Avalanche Current	17	A
P_D@T_C=25°C	Total Power Dissipation[4]	62.5	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State)[1]	--	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	--	2	°C/W

QM18N20D

N-Channel Electrical Characteristics

N-Channel Electrical Characteristics: (T_J=25 ℃, unless otherwise noted)						
Symbol	**Parameter**	**Conditions**	**Min**	**Typ**	**Max**	**Unit**
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	200	--	--	V
$\triangle BV_{DSS} / \triangle T_J$	BVDSS Temperature Coefficient	Reference to 25°C , I_D=1mA	--	0.17	--	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=12A	--	150	190	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2	--	5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		--	-5.2	--	mV/°C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=160V , V_{GS}=0V, T_J=25°C	--	--	2	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±30V , V_{DS}=0V	--	--	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=12A	--	18.8	--	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	--	3.2	6.4	Ω
Q_g	Total Gate Charge	V_{DS}=160V , V_{GS}=10V , I_D=12A	--	19.7	27.6	nC
Q_{gs}	Gate-Source Charge		--	6.9	9.7	
Q_{gd}	Gate-Drain Charge		--	4.7	6.6	
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=100V , V_{GS}=10V , R_G=3.3Ω, I_D=12A	--	10.8	21.6	ns
t_r	Rise Time		--	23	41.4	
$t_{d(off)}$	Turn-Off Delay Time		--	21	42	
t_f	Fall Time		--	16	32	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , F=1MHz	--	1190	1666	pF
C_{oss}	Output Capacitance		--	115	161	
C_{rss}	Reverse Transfer Capacitance		--	4	5.6	

QM18N20D

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=50V , L=1mH , I_{AS}=12A	93	--	--	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current [1,6]	V_G=V_D=0V, Force Current	--	--	18	A
I_{SM}	Pulsed Source Current[2,6]		--	--	36	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25°C	--	--	1	V
t_{rr}	Reverse Recovery Time	I_F=10A , di/dt=100A/μs , T_J=25°C	--	110	--	nS
Q_{rr}	Reverse Recovery Charge		--	525	--	nC

Note:

1. Test data conducted with surface mount attachment to 1 inch^2, FR-4 board utilizing 2oz copper
2. Pulse Test. Pulse width ≦ 300uS, duty cycle ≦ 2%
3. EAS data is a maximum rating. The test condition is V_{DD}=50V,V_{GS}=10V,L=1mH
4. The power dissipation is limited by a 150°C maximum junction temperature
5. The Min. value is 100% EAS tested guarantee
6. The data is theoretically the same as I_D and I_{DM}. In real applications, it will be limited by total power

QM18N20D

Typical Characteristics

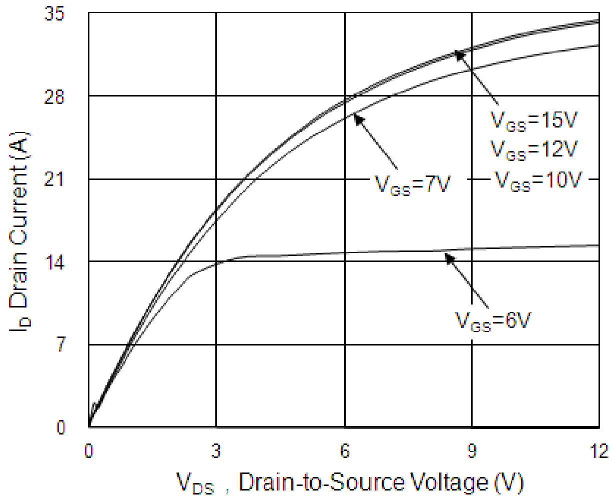


Fig.1: Typical Output Characteristics

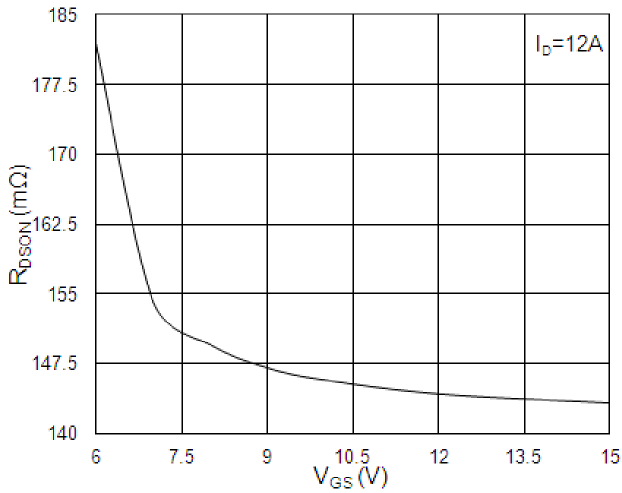


Fig.2: On-Resistance vs. G-S Voltage

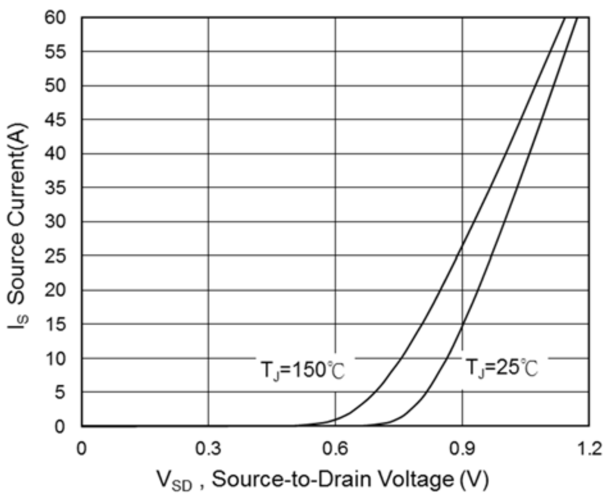


Fig.3: Forward Characteristics of Reverse

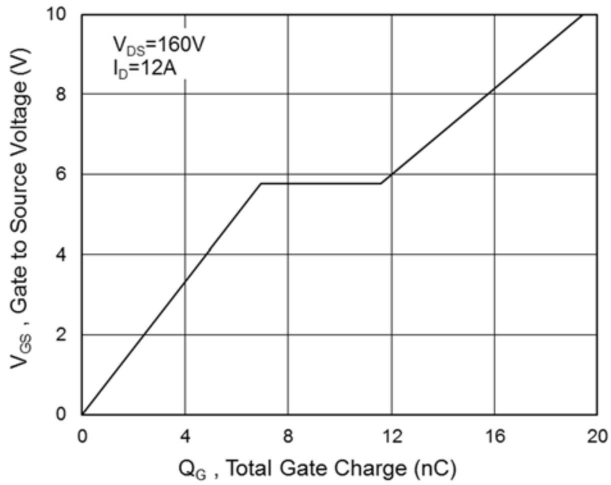


Fig.4: Gate-Charge Characteristics

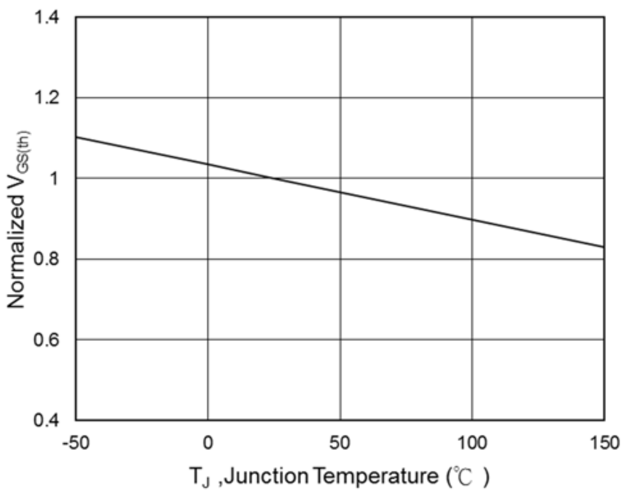


Fig.5: Normalized $V_{GS(th)}$ vs. T_J

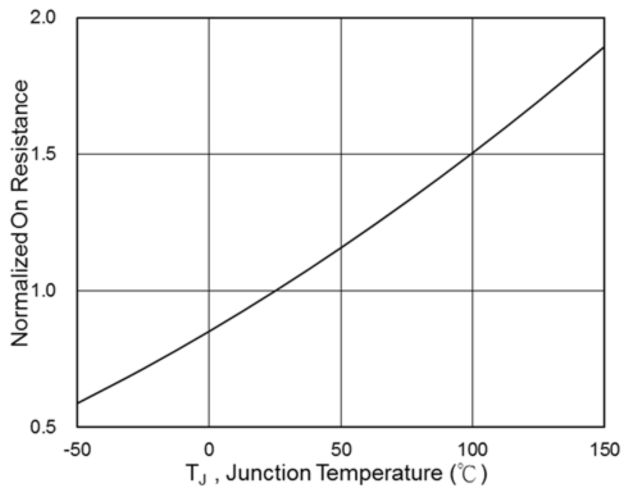


Fig.6: Normalized R_{DSON} vs. T_J

QM18N20D

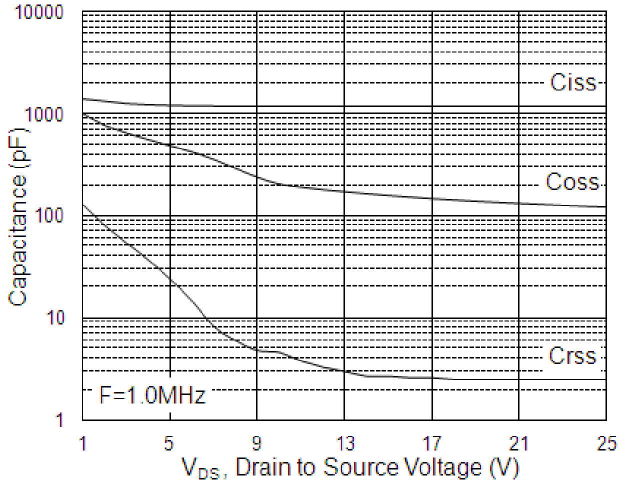


Fig.7: Capacitance

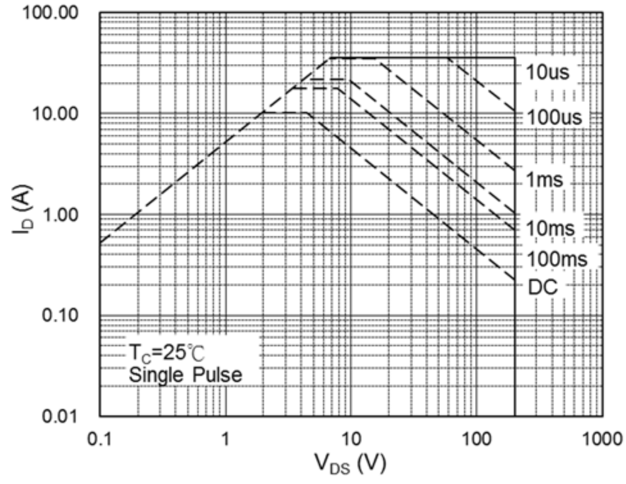


Fig.8: Safe Operating Area

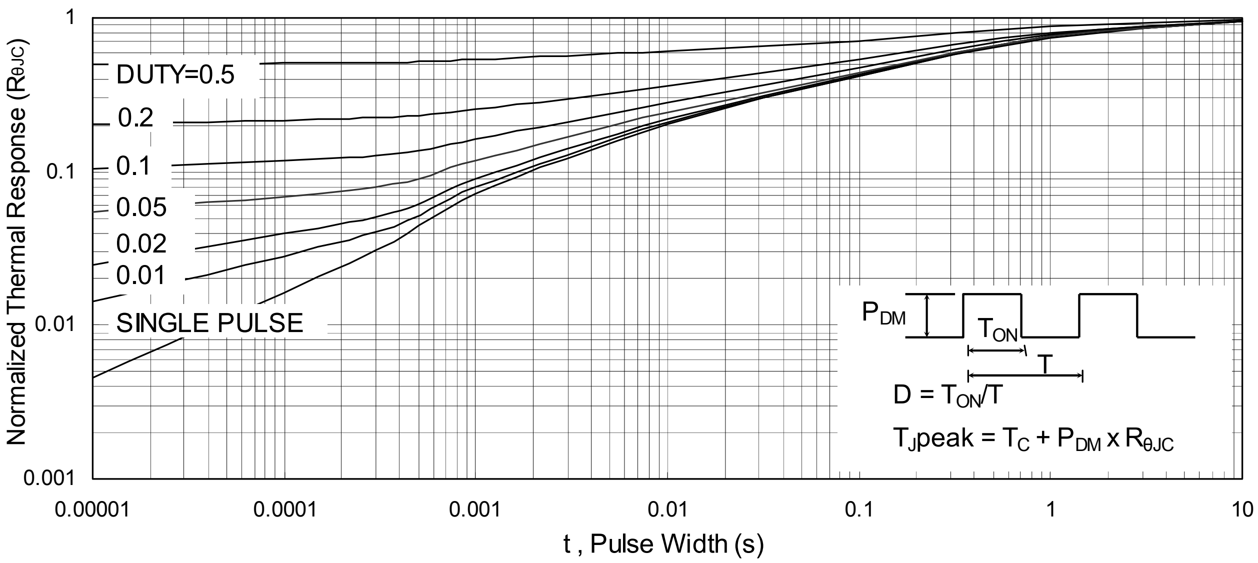


Fig.9: Normalized Maximum Transient Thermal Impedance

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